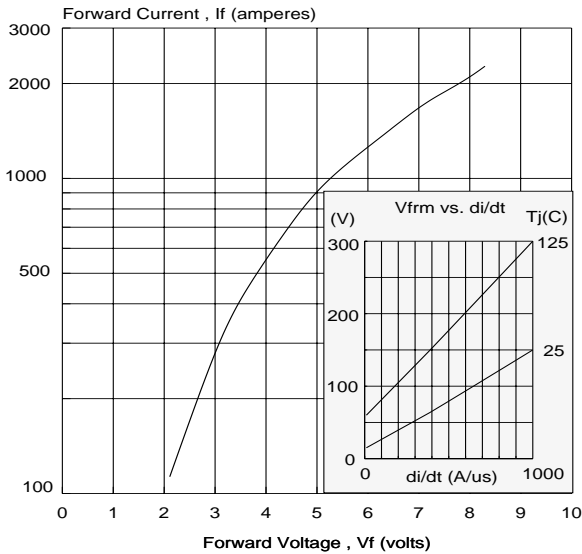


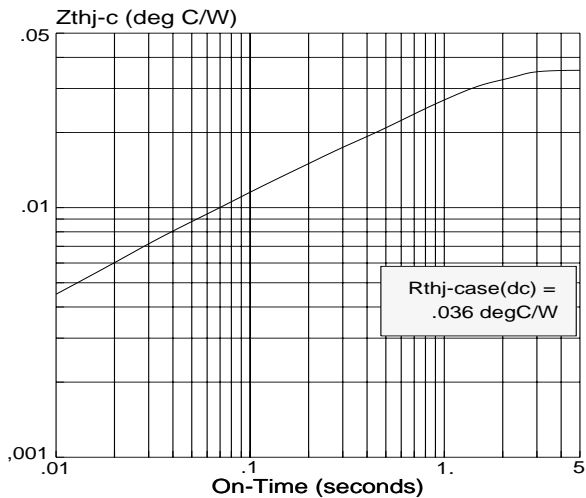
The SDD67HK fast recovery diode is designed as a parallel mate for GTO's used in voltage fed inverter circuits normally requiring the bypass function. Its relatively low recovery current and charge in combination with low thermal resistance offer a new advantage for optimizing other circuit components. It is manufactured by the proven multi-diffusion process with 40mm diameter silicon and is supplied in a disc-type package ready to mount using commercially available heat dissipators and clamping hardware.

FORWARD CHARACTERISTIC  
Process Maximum @  $T_j=125\text{ C}$



91C-3/17/91

THERMAL IMPEDANCE vs. ON-TIME

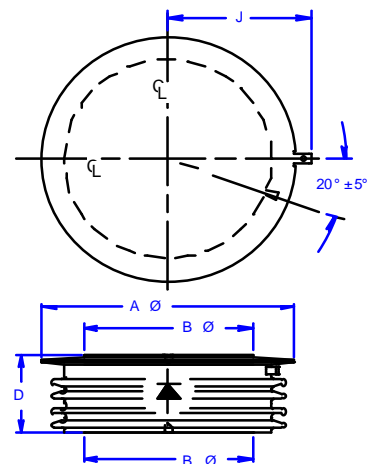


**MAXIMUM RATINGS & PARAMETERS**

Maximum repetitive peak reverse voltage	$V_{RRM}$	$T_j = -40$ to $+125^\circ\text{C}$	to 4500	V
Maximum forward average & RMS current ratings	$I_{P(AV)}$ $I_{RMS}$	$T_{case} 70^\circ\text{C}$	300 470	A
Maximum reverse leakage current	$I_{RRM}$		75	ma
Forward voltage drop	$V_{FM}$	$I_T=1000A$ $t_f=8.3ms$ $T_j=125^\circ\text{C}$	5.30	V
Maximum peak recovery current*	$I_{RR}$	@ 50 A/us @ 100 A/us	120 200	A
Maximum recovery charge *	$Q_{RR}$	@ 50 A/us @100A/us	290 400	$\mu\text{C}$
Typical recovery time and snap factor	$t_{RR}$		4 0.5	$\mu\text{s}$

\*( tested with 3F GTO snubber)

**MECHANICAL OUTLINE**



AF = 2.30 in (58.0 mm)  
BF = 1.35 in (34.3 mm)  
D = 1.04 in (26.4 mm)

CLAMPING FORCE REQUIRED  
2500 - 4200 lb / 11.1 - 18.7 kN